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APPLICATION NO.		FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
				FIRST NAMED INVENTOR	ATTORNET BOCKET NO.	CONFIRMATION NO.	
09/334,646		06/17/1999		SHUNPEI YAMAZAKI	0756-1984	5565	
31780	75	90	02/11/2003				
	ROBINS	SON		EXAMINER			
	SOUTHE	BANK ST.			HU, SHOU	SHOUXIANG	
POTOMAC FALLS, VA 20165			20165		ART UNIT	PAPER NUMBER	
					2811		
					DATE MAILED: 02/11/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.		Applicant(s)	WIV				
		09/334,646		YAMAZAKI ET AL					
	Office Action Summary	Examiner		Art Unit					
•		Shouxiang Hu		2811					
Period for	- The MAILING DATE of this communication app r Reply	ears on the cover	sheet with the c	orrespond nce ad	dress				
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).  Status									
1)⊠	Responsive to communication(s) filed on <u>02 L</u>	December 2002 .							
2a) <u></u> □	This action is <b>FINAL</b> . 2b)⊠ Thi	s action is non-fir	nal.						
3) Since this application is in condition for allowance except for formal matters, prosecution as to the ments is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.  Disposition of Claims									
·	Claim(s) <u>See Continuation Sheet</u> is/are pendir	g in the applicati	on.						
	la) Of the above claim(s) is/are withdrav	vn from considera	ation.						
5) Claim(s) is/are allowed.									
6)	Claim(s) <u>1-3,8,11-14,16-19,32-34,38-43,52,53,</u>	<u>58-60,65,71-73,7</u>	5-81 and 100-1	21 is/are rejected.					
	Claim(s) is/are objected to.								
	Claim(s) are subject to restriction and/or	election requirer	ment.						
-	on Papers	•							
9)⊠ The specification is objected to by the Examiner.									
10)∐ T	he drawing(s) filed on is/are: a)☐ accep	ted or b) objecte	ed to by the Exar	niner.					
	Applicant may not request that any objection to the	e drawing(s) be held	d in abeyance. Se	ee 37 CFR 1.85(a).					
11) 🔲 T	he proposed drawing correction filed on	is: a)∏ approve	d b) disappro	ved by the Examin	er.				
If approved, corrected drawings are required in reply to this Office action.									
12)☐ The oath or declaration is objected to by the Examiner.									
Priority under 35 U.S.C. §§ 119 and 120									
13)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).									
a)⊠ All b)□ Some * c)□ None of:									
	1. Certified copies of the priority documents	s have been rece	ived.						
	2. Certified copies of the priority documents	s have been rece	ived in Application	on No. <u>08/513,09</u> 6	<u>0</u> .				
<ul> <li>Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>									
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).									
a) The translation of the foreign language provisional application has been received.									
15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.									
Attachment	• •	( <del></del> )			, , <b>, , , ,</b>				
2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s)	4) <b>[K</b> ] 5) <b>[</b> 6) <b>[</b>		(PTO-413) Paper No Patent Application (PT					
J.S. Patent and Tra	ademark Office								

Continuation Sheet (PTO-326)

Continuation of Disposition of Claims: Claims pending in the application are 1-3,8,11-14,16-19,32-34,38-43,52,53,58-60,65,71-73,75-81 and 100-121.

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### **DETAILED ACTION**

1. This application is a divisional of U.S. Application No. 08/938,310, filed on September 26, 1997, now U.S. Patent 5,959,313, which itself is a divisional of U.S. Application No. 08/513,090, filed on August 9, 1995, now U.S. Patent 5,731,613.

#### Claim Cancellation

2. Claims 82-99 were canceled by Applicant in Paper No. 22. In addition, claims 6, 26-28, 48, 49, 63 and 74 were canceled in Amendment E (Paper No. 16) filed by Applicant on April 13, 2001.

Accordingly, claims 1-3, 8, 11-14, 16-19, 32-34, 38-43, 52, 53, 58-60, 65, 71-73, 75-81 and 100-121 are currently pending and active.

### Claim Objections

3. Claims 104-121 are objected to because of the following informalities and/or defects:

In claims 104 and 113, the term of "each respective second thin film transistor" should read as --each respective said second thin film transistor--.

In claims 107 and 116, the term of "each respective second thin film transistor" should read as --each respective second thin film transistor of said some of the plurality of second thin film transistors--.

In claims 110 and 119, the term of "each respective second thin film transistor" should read as –said at least one of the plurality of second thin film transistors—.

Appropriate correction is required.

### Claim Rejections - 35 USC § 112

- 4. The following is a quotation of the first paragraph of 35 U.S.C. 112:
  - The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.
- 5. Claims 106, 109, 112, 115, 118 and 121 are rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. Each of these claims recites the subject matter that the recited semiconductor layer is a polycrystalline layer formed through the laser annealing. But, no support for it can be found in the original disclosure, which clearly discloses that the semiconductor layer is a monocrystalline one (see the paragraph crossover pages 19 and 20).

## Claim Rejections - 35 USC § 103

- 6. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

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invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

7. Claims 1-3, 8, 11-14, 16-19, 32-34, 38-43, 52, 53, 58-60, 65, 71-73, 75-81 and 100-103 are rejected under 35 U.S.C. 103(a) as being unpatentable over Zhang et al. ("Zhang"; US 5,403,772) in view of Kuribayashi et al. ("Kuribayashi"; US 5,233,447) and/or Matsueda (US 5,173,792).

Zhang discloses an active matrix type LC display device (Figs. 1-8A, particularly, Fig. 8A), comprising: a pixel matrix portion (104) having a plurality of pixels on an insulating substrate (107); and a peripheral driver circuit portion (101 and 102) on the same insulation substrate, thin film transistors (TFTs) in the driver circuit portion each having a channel forming region in one of the separate semiconductor layers (11a and 11b) provided on an insulating surface, wherein the channel forming region is provided in a region which can be regarded as effectively monocrystalline silicon (see col. 6, lines 13-15); and, the channel forming region contains impurities (a type of point defects) of carbon, nitrogen and oxygen at a concentration less than 10<sup>18</sup> cm<sup>-3</sup>, which meets the limitation of each channel forming region "containing carbon and nitrogen at a concentration of 5x10<sup>18</sup> cm<sup>-3</sup> or less, respectively, and containing oxygen at a concentration of 5x10<sup>19</sup> cm<sup>-3</sup> or less, recited in the claimed invention.

It is noted that, since the channel forming region in Zhang is formed with a method which is substantially the same as the one used in the claimed invention, the method used in Zhang is regarded as being inherently capable of forming the channel forming region having no linear defects or surface defects. In addition, one of ordinary skill in the art would readily recognize that it is always desirable to form the channel

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forming region having no linear defects or surface defects for achieving good channel performance.

Although Zhang does not expressly disclose that the display device further comprises a buffer circuit in the driver circuit, one of ordinary skill in the art would readily recognize that such a buffer circuit is normally required for achieving desired driving output, as evidenced in Kuribayashi (see the buffer circuit (81) in Fig. 8; also see col. 8, lines 56-66). It is also evidenced in Kuribayashi (see Fig. 19) that an active matrix type display device commonly further comprises a memory, a decode and a display system for maintaining its basic display functionality.

Zhang does not expressly disclose that the peripheral driver circuit portion comprises at least two TFTs connected in parallel. Matsueda discloses an active matrix type LC display device (Figs. 1-12, particularly, Fig. 7), comprising: at least two TFTs (100A and 100B) provided on the surface of an insulating layer (110); a common gate wire (102); a common source wire (Xm); a common drain wire (101), wherein the channel forming regions of the parallel-connected transistors are provided in separate semiconductor layers respectively. Matsueda teaches that the reliability of a basic control element comprising two or more parallel-connected TFTs is better than that of a basic control element comprising a single TFT.

It would therefore have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the parallel-connected TFTs of Matsueda into the driver circuit in the display device of Zhang with the driver circuit including a buffer circuit, per the teaching of Kuribayashi, so that a display device having both pixel and

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driver portions formed on a same insulating substrate with good reliability in both of them would be obtained.

Regarding claims 11-14, 16-19 and 32-34, as mentioned above, an active matrix type display device commonly further comprises a memory, a decode and a display system for maintaining its basic display functionality.

Regarding claims 38-43, 52, 53, 58-60 and 65, it is noted that it is well known in the art that the carrier mobility and crystallization quality are strongly correlated with the Raman spectrum width ratio and intensity ratio, as evidenced in the prior art such as in Fig. 3 of Yamazaki et a. (5,608,232), which shows that the Raman spectrum width ratio of W/W<sub>0</sub> is 2.0 or less; and, that the Raman spectrum intensity ratio of I/I<sub>0</sub> is about 0.8 or more.

It would therefore have been obvious to one of ordinary skill in the art at the time the invention was made to make the device collectively taught by Zhang, Kuribayashi and Matsueda with the Raman spectrum width ratio of W/W<sub>0</sub> being 2.0 or less and the Raman spectrum intensity ratio of I/I<sub>0</sub> being about 0.8 or more, so that improved display device performance with high-mobility TFTs would be achieved.

8. Claims 104-121, insofar as being in compliance with 35 U.S.C. 112 and being best understood in view of the above claim objections, are rejected under 35 U.S.C. 103(a) as being unpatentable over Zhang et al. ("Zhang"; US 5,403,772) in view of Matsueda (US 5,173,792).

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Zhang discloses an active matrix type LC display device (Figs. 1-8A, particularly, Fig. 8A), comprising: a pixel portion (104) having plurality of first thin film transistors (TFTs) connected respectively to a plurality of pixel electrodes formed on (or over) an insulating substrate (107; see Fig. 8(A)); and a plurality of second TFTs forming a driver circuit (101 and/or 102) for driving the pixel portion.

Zhang does not expressly disclose that each (or some, or at least one) of the second TFTs comprising a plurality of channel areas connected in parallel.

However, Matsueda discloses an active matrix type LC display device (Figs. 1-12, particularly, Fig. 7), comprising a TFT with a plurality of channel areas (in 100A and 100B, separated in the channel width direction) electrically connected in parallel.

Matsueda teaches that the reliability of a basic control element comprising a plurality of parallel-connected channel areas is better than that of a basic control element comprising a single channel area.

It would therefore have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the parallel-connected channel areas of Matsueda into both of the first and second TFTs of Zhang, so that a display device having both pixel and driver portions formed on a same insulating substrate with good reliability in both of them would be obtained. In addition, the limitation of "subject to laser annealing respectively" as recited in the claims is a process limitation. And, it would not carry patentable weight in the claims drawing to a structure, because distinct structure is not necessarily produced. In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985).

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### Response to Arguments

9. Applicant's arguments filed on December 2, 2002, have been fully considered but they are not persuasive.

In response to applicant's argument that there is no suggestion to combine the references as Matsueda only teaches to have parallel-connected TEFs in the pixel portion, the examiner recognizes that obviousness can only be established by combining or modifying the teachings of the prior art to produce the claimed invention where there is some teaching, suggestion, or motivation to do so found either in the references themselves or in the knowledge generally available to one of ordinary skill in the art. See In re Fine, 837 F.2d 1071, 5 USPQ2d 1596 (Fed. Cir. 1988) and In re Jones, 958 F.2d 347, 21 USPQ2d 1941 (Fed. Cir. 1992). In this case, Kuribayashi teaches that an active matrix type display device commonly comprises a buffer circuit, a memory, a decode and a display system for maintaining its basic display functionality. And, Matsueda teaches that the reliability of a basic control element comprising two or more parallel-connected TFTs is better than that of a basic control element comprising a single TFT. With these teachings along with the further teachings of Zhang that the driver portion and the pixel portion are both formed on a same insulating substrate, one of ordinary skill in the art would readily recognize that the reliability of the display device of Zhang would be improved if the TFTs in both of the pixel portion and the driver portion are formed of two of more parallel-connected TFTs.

In response to applicant's argument that Applicant's claimed invention yields advantages of high voltage resistance and high speed performance by solving problems

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which Matsueda fails to recognize, the fact that applicant has recognized another advantage which would flow naturally from following the suggestion of the prior art cannot be the basis for patentability when the differences would otherwise be obvious. See *Ex parte Obiaya*, 227 USPQ 58, 60 (Bd. Pat. App. & Inter. 1985). In this case, as explained above, it is regarded as being obvious to one of ordinary skill in the art at the time the invention was made to incorporate the parallel-connected TFTs of Matsueda into the driver circuit in the display device of Zhang for achieving better reliability in the display device; and the advantages of high voltage resistance and high speed performance would flow naturally from the incorporation of the parallel-connected TFTs into the driver circuit.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shouxiang Hu whose telephone number is (703) 306-5729. The examiner can normally be reached on Monday through Thursday, 7:30 AM to 6:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9318 for regular communications and (703) 872-9319 for After Final communications.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

SH

February 9, 2003

Shows ang Ru
Shouxiang Hu
Patent Examiner
TC2800